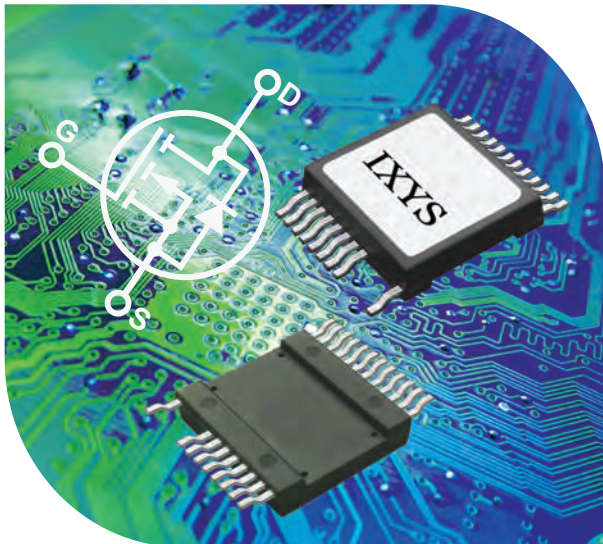


Reduce The Size of Your High Power Design

1000V Q3-Class HiPerFET™ Power MOSFET in SMPD Package Technology



Q3-Class HiPerFET™ Features:

- Low $R_{ds(on)}$ & Q_g
- Low Intrinsic Gate Resistance
- Fast Intrinsic Rectifier
- Excellent dV/dt Performance
- High Avalanche Energy Capabilities
- High Speed Switching Capabilities
- High Noise Immunity

Applications:

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- Temperature and Lighting Controls

SMPD Package Features:

- Compact, Ultra-low Package Profile (5.3mm height x 24.8mm length x 32.3mm width)
- 2500V Ceramic Isolation (DCB)
- Very High Power Cycling Capability
- Excellent Thermal Performance
- Low Package Weight (8g)
- High Power Density

Part Number	VDSS Max (V)	ID(cont) TC=25°C (A)	RDS(on) max TJ=25°C (Ω)	Ciss Typ (pF)	Qg Typ (nC)	trr Max (ns)	PD (W)	RthJC Max (°C/W)	Package Style
MMIX1F44N100Q3	1000	30	0.245	13600	264	300	694	0.18	SMPD

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Efficiency Through Technology

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